(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
2 March 2006 (02.03.2006)

PCT

(10) International Publication Number
WO 2006/022765 A1

(51) International Patent Classification[7]: H01L 21/8242

(21) International Application Number:
PCT/US2004/034587

(22) International Filing Date: 19 October 2004 (19.10.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/925,789 24 August 2004 (24.08.2004) US

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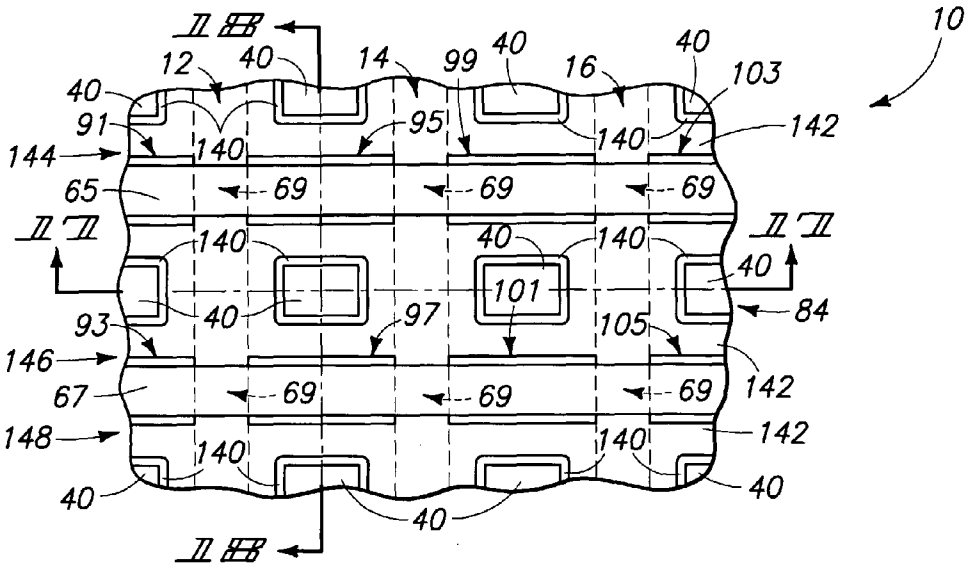
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *with amended claims*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR CONSTRUCTION WITH ISOLATION REGIONS FOR DRAM CELL AND PRODUCTION METHOD



(57) Abstract: The invention includes semiconductor constructions containing vertically-extending pillars (80, 82) and methods for forming such constructions. The vertically-extending pillars can be incorporated into transistor devices (80, 95) and can contain vertically-extending channel regions of the transistor devices. The transistor devices can be incorporated into integrated circuitry, and in some aspects are incorporated into memory constructions, such as, for example, dynamic random access memory (DRAM) constructions.

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